



## 45W,28V Plastic RF LDMOS Transistor

**ITEH09045C6**

### Description

The ITEH09045C6 is a 45-watt, highly rugged, LDMOS transistor, designed for any general applications at frequencies up to 1GHz, in 10\*6mm QFN plastic package, supporting surface mounted on PCB through high density grounding vias.

**It can be tuned to meet 35-36dBm WCDMA or LTE ACLR without DPD needed purely by back off operation.**



• Typical 758-803MHz Class AB RF Performance (On Innegration fixture with device soldered).

**$V_{ds}=28V$ ,  $I_{dq}=250mA$ ,  $V_{gs}=2.6V$  WCDMA 1C-PAR10.8**

Freq (MHz)	Pout (dBm)	CCDF (dB)	ACPR (dBc)	Gain (dB)	Efficiency (%)
758	36	9.55	-46.4	20.1	22.2
780	36	9.57	-46.3	20.2	22.2
803	36	9.51	-47.6	19.8	22.5

### Features

- High Efficiency and Linear Gain Operations
- Integrated ESD Protection
- Excellent thermal stability, low HCI drift
- Large Positive and Negative Gate/Source Voltage Range for Improved Class C Operation
- Pb-free, RoHS-compliant

### Suitable Applications

- P band power amplifier
- All 4G/5G cellular application within 0.7 to 1GHz

**Table 1. Maximum Ratings**

Rating	Symbol	Value	Unit
Drain--Source Voltage	$V_{DSS}$	+65	Vdc
Gate--Source Voltage	$V_{GS}$	-10 to +10	Vdc
Operating Voltage	$V_{DD}$	+28	Vdc
Storage Temperature Range	$T_{stg}$	-65 to +150	°C
Case Operating Temperature	$T_C$	+150	°C
Operating Junction Temperature	$T_J$	+225	°C

**Table 2. Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case $T_C=85^\circ\text{C}$ , DC test	$R_{\theta JC}$	2	°C/W

**Table 3. ESD Protection Characteristics**

Test Methodology	Class
Human Body Model (per JESD22--A114)	Class 2



**Table 4. Electrical Characteristics** (TA = 25 °C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>DC Characteristics</b>					
Drain-Source Voltage $V_{GS}=0, I_{DS}=100\mu A$	$V_{(BR)DSS}$		65		V
Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 28V, V_{GS} = 0V$ )	$I_{DSS}$	—	—	1	$\mu A$
Gate--Source Leakage Current ( $V_{GS} = 11V, V_{DS} = 0V$ )	$I_{GSS}$	—	—	1	$\mu A$
Gate Threshold Voltage ( $V_{DS} = 28V, I_D = 600\mu A$ )	$V_{GS(th)}$	—	2	—	V
Gate Quiescent Voltage ( $V_{DD} = 28V, I_D = 250mA$ , Measured in Functional Test)	$V_{GS(O)}$	—	2.6	—	V

**Load Mismatch (In Innegration Test Fixture, 50 ohm system):**  $V_{DD} = 28Vdc, I_{DQ} = 250mA, f = 800MHz$

VSWR 10:1 at 45W pulse CW Output Power	No Device Degradation
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**Figure 1: Pin Definition (Top View)**



Pin No.	Symbol	Description
8,9,10,11,14,15,16,17	Vgs/RF In	Vgs and RF input
26,27,28,29,32,33,34,35	Vds/RF out	Vds and RF output
2,5,7,12,13,18,20,23,25,30,31,36	GND	DC/RF Ground
Others	NC	No connection
Package Base	GND	DC/RF Ground.

## 758-803MHz application board

### Reference Circuit of Test Fixture Assembly Diagram 20mils RO4350B

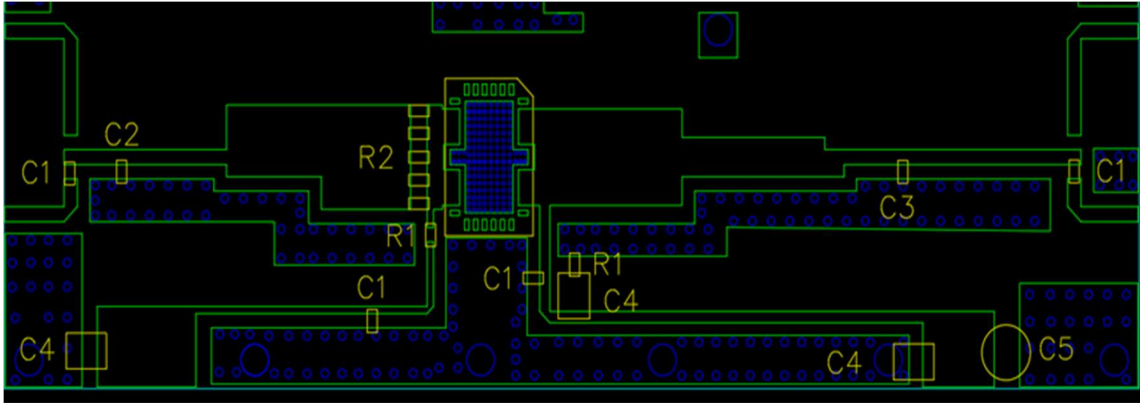


Figure 2. Test Circuit Component Layout

Table 5. Test Circuit Component Designations and Values

Component	Value	Quantity
U1	ITEH09045C6	1
C1	68pF	4
C4	10uF/63V	3
R1	10 Ω	2
R2	15 Ω	5
C5	470uF/63V	1
C2	8.2pF	1
C3	6.8pF	1

### TYPICAL CHARACTERISTICS

Figure 3. Power Gain and Drain Efficiency as function of Power Output

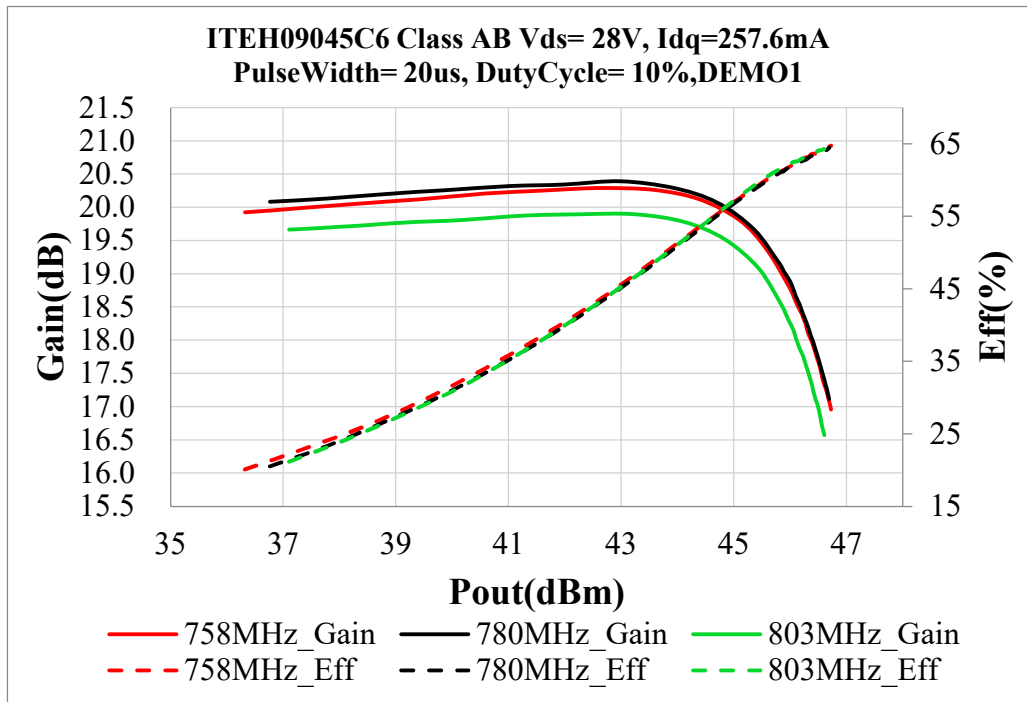


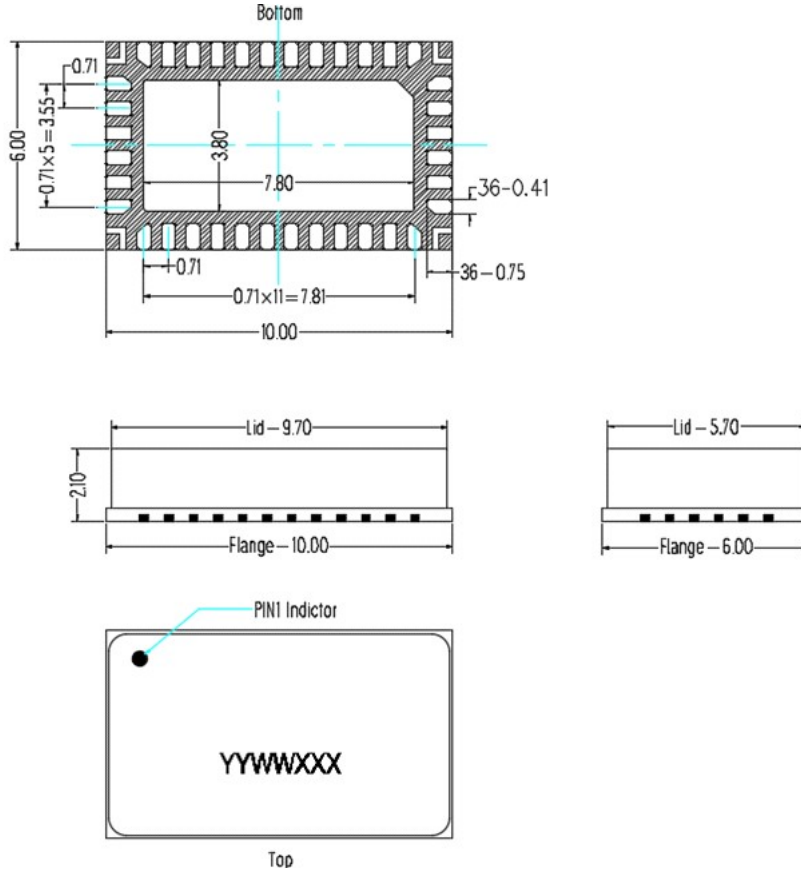
Figure 4. Network analyzer output S11/S21





### Package Dimensions

#### 10\*6 Plastic Package



#### Notes:

1. All dimensions are in mm;
2. The tolerances unless specified are  $\pm 0.2$ mm.

### Revision history

Table 7. Document revision history

Date	Revision	Datasheet Status
2023/02/03	Rev 1.0	Preliminary Datasheet

#### Application data based on ZYX-23-02

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